Product data sheet

1. General description

PNP low V_{CEsat} transistor in a SOT89 (SC-62/TO-243) small and flat lead Surface-Mounted Device (SMD) plastic package.

NPN complement: PBSS302NX

2. Features and benefits

- · Low collector-emitter saturation voltage VCEsat
- High collector current capability I_C and I_{CM}
- High collector current gain (h_{FE}) at high I_C
- · High efficiency due to less heat generation
- Smaller required Printed-Circuit Board (PCB) area than for conventional transistors
- AEC-Q101 qualified

3. Applications

- DC-to-DC conversion
- MOSFET gate driving
- Motor control
- Charging circuits
- Power switches (e.g. motors, fans)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	-20	V
I _C	collector current		-	-	-5.1	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms	-	-	-10.2	Α
R _{CEsat}	collector-emitter saturation resistance	I_C = -4 A; I_B = -200 mA; pulsed; $t_p \le$ 300 μs; $\delta \le$ 0.02; T_{amb} = 25 °C	-	32	48	mΩ



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	Е	emitter		С
2	С	collector		, , , , , , , , , , , , , , , , , , ,
3	В	base	3 2 1	B—[
			SOT89	sym132

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PBSS302PX		plastic, surface-mounted package; 3 leads; 1.5 mm pitch; 4.5 mm x 2.5 mm x 1.5 mm body	SOT89		

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
PBSS302PX	%5J

[1] % = placeholder for manufacturing site code

8. Limiting values

Table 5. Limiting values

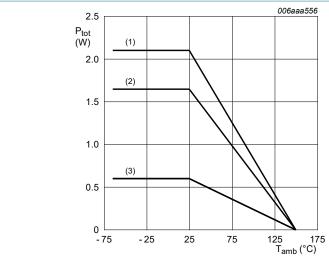
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter		-	-20	V
V_{CEO}	collector-emitter voltage	open base		-	-20	V
V_{EBO}	emitter-base voltage	open collector		-	-5	V
I _C	collector current			-	-5.1	А
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-10.2	А
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	0.6	W
			[2]	-	1.65	W
			[3]	-	2.1	W
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	150	°C
T _{stg}	storage temperature			-65	150	°C

- 1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- [3] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.

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- (1) Ceramic PCB, Al₂O₃, standard footprint
- (2) FR4 PCB, mounting pad for collector 6 cm²
- (3) FR4 PCB, standard footprint

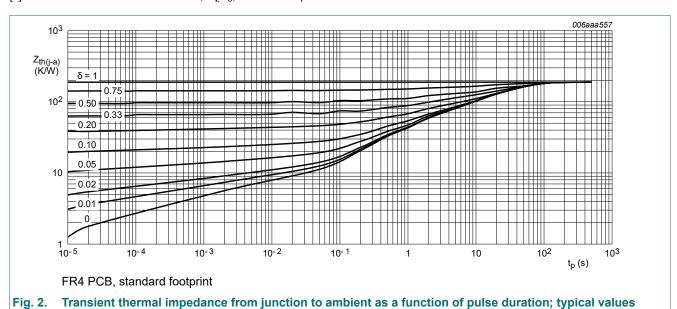
Fig. 1. Power derating curves

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)} thermal resistance from junction to ambient	in free air	[1]	-	-	208	K/W	
	junction to ambient		[2]	-	-	76	K/W
			[3]	-	-	60	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	20	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- [3] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.



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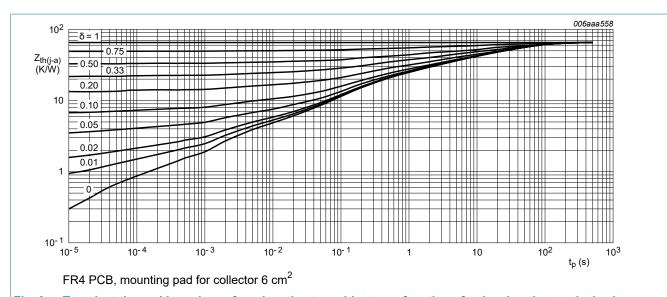


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

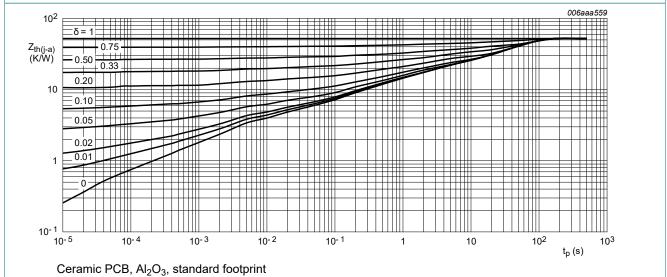


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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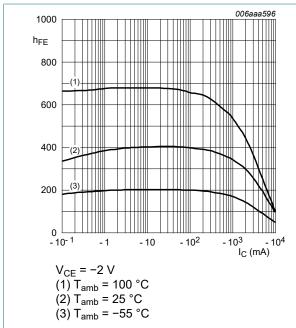
10. Characteristics

Table 7. Characteristics

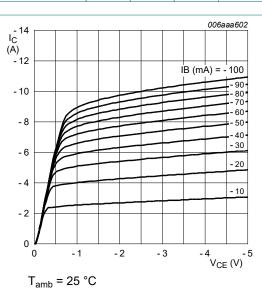
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	V _{CB} = -20 V; I _E = 0 A; T _{amb} = 25 °C	-	-	-100	nA
	current	V _{CB} = -20 V; I _E = 0 A; T _j = 150 °C	-	-	-50	μA
ЕВО	emitter-base cut-off current	V _{EB} = -5 V; I _C = 0 A; T _{amb} = 25 °C	-	-	-100	nA
1 _{FE}	DC current gain	V_{CE} = -2 V; I_{C} = -0.5 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	250	370	-	
		V_{CE} = -2 V; I_{C} = -1 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	250	340	-	
		V_{CE} = -2 V; I_{C} = -2 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	200	290	-	
		V_{CE} = -2 V; I_{C} = -4 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	150	220	-	
		V_{CE} = -2 V; I_{C} = -6 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	100	160	-	
OLOGI	collector-emitter saturation voltage	I_C = -0.5 A; I_B = -50 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-25	-35	mV
		I_C = -1 A; I_B = -50 mA; pulsed; $t_p \le$ 300 μs; $\delta \le$ 0.02; T_{amb} = 25 °C	-	-45	-65	mV
		I_C = -1 A; I_B = -10 mA; pulsed; $t_p \le$ 300 μs; $\delta \le$ 0.02; T_{amb} = 25 °C	-	-70	-100	mV
		I_C = -2 A; I_B = -40 mA; pulsed; $t_p \le$ 300 μs; $\delta \le$ 0.02; T_{amb} = 25 °C	-	-90	-130	mV
		I_C = -4 A; I_B = -200 mA; pulsed; $t_p \le$ 300 μs; $\delta \le$ 0.02; T_{amb} = 25 °C	-	-130	-190	mV
		I_C = -4 A; I_B = -400 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-120	-175	mV
		I_C = -4 A; I_B = -40 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-200	-300	mV
		I_C = -5.1 A; I_B = -255 mA; pulsed; $t_p \le$ 300 μs; $\delta \le$ 0.02; T_{amb} = 25 °C	-	-160	-230	mV
RCEsat	collector-emitter saturation resistance	I_C = -4 A; I_B = -200 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	32	48	mΩ
		I_C = -4 A; I_B = -40 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	50	75	mΩ
/ _{BEsat}	base-emitter saturation voltage	I_C = -1 A; I_B = -100 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-0.82	-0.9	V
		I_C = -4 A; I_B = -400 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-0.93	-1.05	V
/ _{BEon}	base-emitter turn-on voltage	V_{CE} = -2 V; I_{C} = -2 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-0.76	-0.85	V
d	delay time	V _{CC} = -12.5 V; I _C = -3 A; I _{Bon} = -0.15 A;	-	10	-	ns
г	rise time	I _{Boff} = 0.15 A; T _{amb} = 25 °C	-	55	-	ns
on	turn-on time	300 μs; $\delta \le 0.02$; $T_{amb} = 25$ °C $C_{c} = -5.1$ A; $I_{B} = -255$ mA; pulsed; $t_{p} \le 0.00$ μs; $\delta \le 0.02$; $T_{amb} = 25$ °C $C_{c} = -4$ A; $I_{B} = -200$ mA; pulsed; $t_{p} \le 0.00$ μs; $\delta \le 0.02$; $T_{amb} = 25$ °C $C_{c} = -4$ A; $I_{B} = -40$ mA; pulsed; $t_{p} \le 0.00$ μs; $\delta \le 0.02$; $T_{amb} = 25$ °C $C_{c} = -1$ A; $I_{B} = -100$ mA; pulsed; $t_{p} \le 0.00$ μs; $\delta \le 0.02$; $T_{amb} = 25$ °C $C_{c} = -4$ A; $C_{c} = -400$ mA; pulsed; $C_{c} = -400$ μs; $C_{c} = -400$ mA; pulsed; $C_{c} = -400$ μs; $C_{c} = -400$ mA; pulsed; $C_{c} = -400$ μs; $C_{c} = -200$ N; C_{c}	-	65	-	ns
S	storage time		-	205	-	ns
f	fall time		-	145	-	ns
off	turn-off time		-	350	-	ns

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f _T	transition frequency	V_{CE} = -10 V; I_{C} = -0.1 A; f = 100 MHz; T_{amb} = 25 °C	-	130	-	MHz
C _c	collector capacitance	V_{CB} = -10 V; I_{E} = 0 A; i_{e} = 0 A; f = 1 MHz; T_{amb} = 25 °C	-	130	160	pF



DC current gain as a function of collector Fig. 5. current; typical values



Collector current as a function of collector-Fig. 6. emitter voltage; typical values

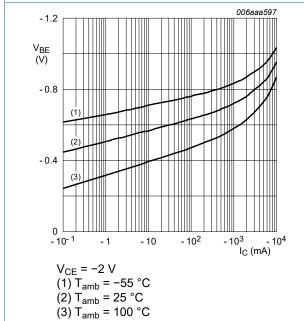
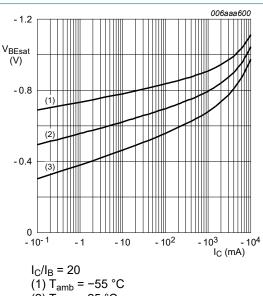


Fig. 7. Base-emitter voltage as a function of collector current; typical values



(2) T_{amb} = 25 °C (3) $T_{amb} = 100 \, ^{\circ}C$

Fig. 8. Base-emitter saturation voltage as a function of collector current; typical values

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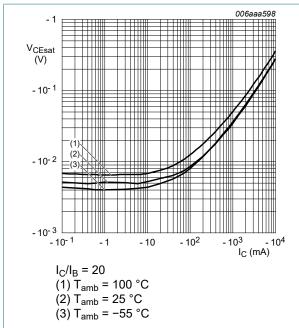


Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values

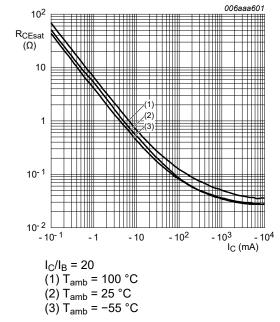


Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values

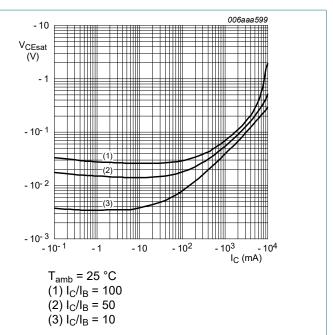


Fig. 10. Collector-emitter saturation voltage as a function of collector current; typical values

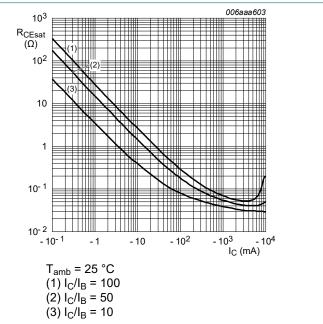
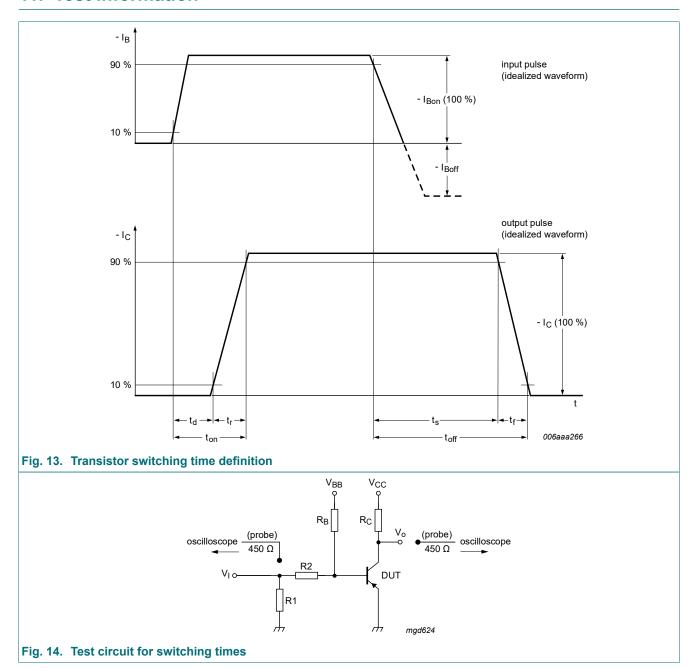


Fig. 12. Collector-emitter saturation resistance as a function of collector current; typical values

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11. Test information

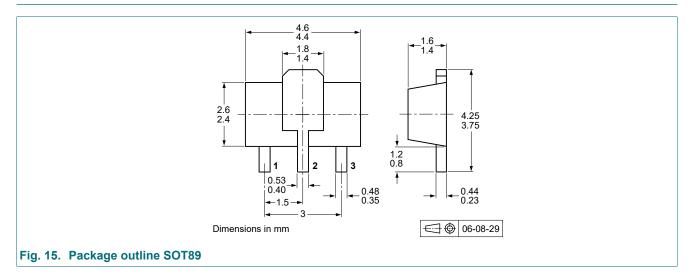


Quality information

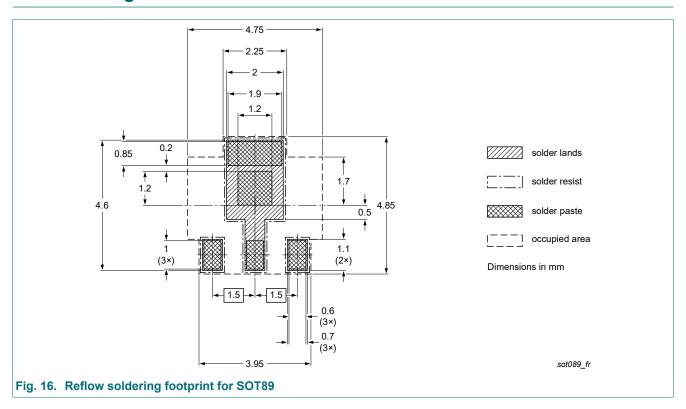
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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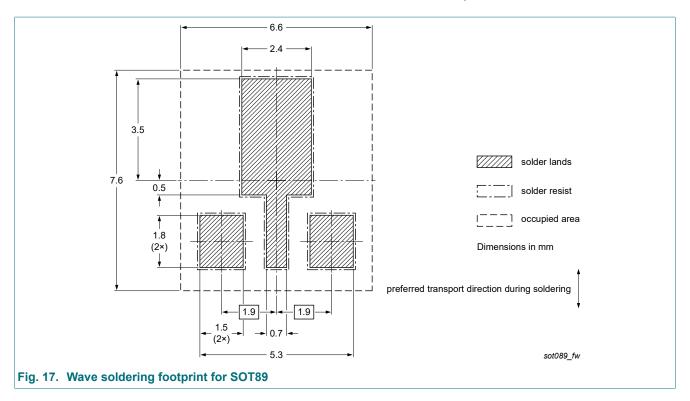
12. Package outline



13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBSS302PX v.3	20240123	Product data sheet	-	PBSS302PX v.2
Modifications:	 The format of this data sheet has been redesigned to comply with the identity guidelines of Nexperia. Legal texts have been adapted to the new company name where appropriate. Section "Packing information" removed. 			
PBSS302PX v.2	20091120	Product data sheet	-	PBSS302PX v.1
PBSS302PX v.1	20060823	Product data sheet	-	-

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15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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